

INTRODUCE:

HVGT brand high voltage silicon rectifier diodes is made of high quality wafer chip and high reliability epoxy resin sealing structure, and through professional testing equipment inspection qualified after to customers.

FEATURES:

1. Design of high quality wafer chip.
2. Fast recovery time.
3. Axial Lead.
4. Medium current design.
5. Epoxy resin molded in vacuum.
6. Have anticorrosion in the surface.
7. ANSI/UL94 V-0 Rated Material.

APPLICATIONS:

1. Detecting equipment.
2. General purpose high voltage rectifier.
3. X-ray voltage doubling circuit.
4. Microwave transmission power supply.

REFERENCE SHAPE:



HVGT SEMI Package Naming: DO-415

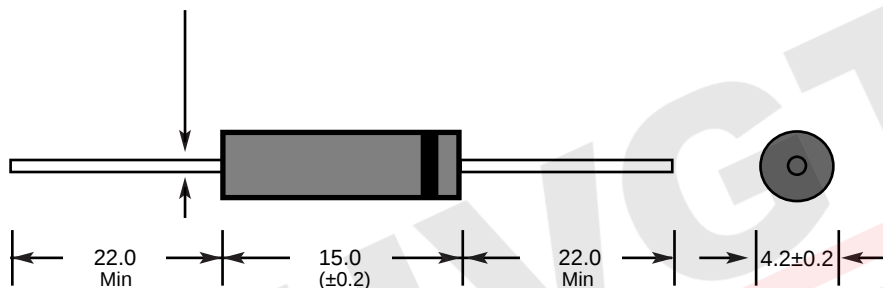
MECHANICAL DATA:

1. Case: epoxy resin molding.
2. Terminal: Axis soft lead.
3. Net weight: 0.65 grams (approx).

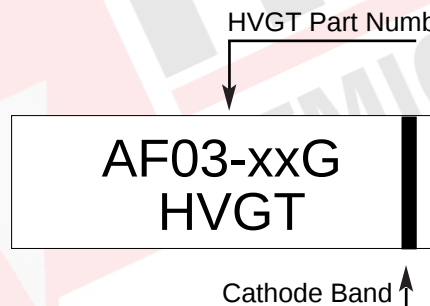
DRAWINGS: (Unit:mm)

DO-415 Series

Lead Diameter 0.8mm ± 0.03



MARKING:



Maximum Ratings And Characteristics: (25°C ambient temperature unless stated otherwise.)

HVGT Part	V _{RRM}	I _{FAVM1}	I _{FAVM2}	V _F	I _{R1}	I _{R2}	I _{FSM}	T _{RR}	C _J
Number	kV	mA	mA	V	uA	uA	A	nS	pF
AF03-15G	15	30	55	30.0	1.0	10	3.0	80	0.5
AF03-20G	20	30	55	35.0	1.0	10	3.0	80	1.0
AF03-25G	25	30	55	40.0	1.0	10	3.0	80	0.9
SF03-30G	30	30	55	45.0	1.0	10	3.0	80	0.8
AF03-35G	35	30	55	48.0	1.0	10	3.0	80	0.7
AF03-40G	40	30	55	50.0	1.0	10	3.0	80	0.6

Temperature:

Storage Temperature: -40 to 125 °C

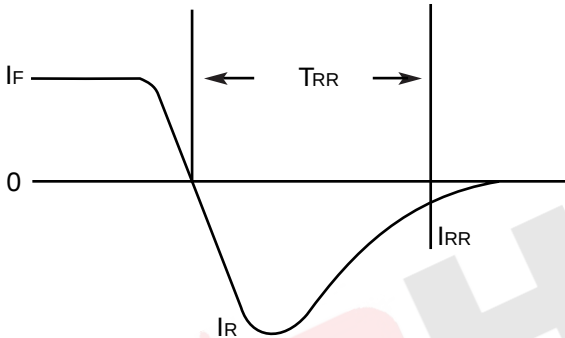
Operating Temperature: -40 to 125 °C

Maximum Junction Temperature: 125 °C

Specification Definitions:

Symbols	Items	Condition
V _{RRM}	Maximum Repetitive Reverse Voltage	--
I _{FAVM1}	Maximum Average Forward Current	At T _A = 55°C
I _{FAVM2}	Maximum Average Forward Current	At T _{oil} = 55°C
V _F	Maximum Forward Voltage Drop	At I _{FAVM}
I _{R1}	Maximum Leakage Current	At V _{RRM} T _A = 25°C
I _{R2}	Maximum Leakage Current	At V _{RRM} T _A = 100°C
I _{FSM}	Maximum Surge Current	At 60Hz, 8.3 mS, Single Half Sine
T _{RR}	Maximum Reverse Recovery Time	I _F = 0.5 I _{FAVM} ; I _R = -I _{FAVM} ; I _{RR} = -0.25 I _{FAVM}
C _J	Typical Junction Capacitance	At V _R = 0VDC, f = 1MHz

FIGURE 01 Reverse Recovery Measurement Waveform



Typical data capture points: $I_F = 0.5I_R$, $I_R, I_{RR} = 0.25I_R$
 I_R is typically the rated average forward current maximum (I_{FAVM}) of the D.U.T.

FIGURE 02 Forward Current Derating Curve

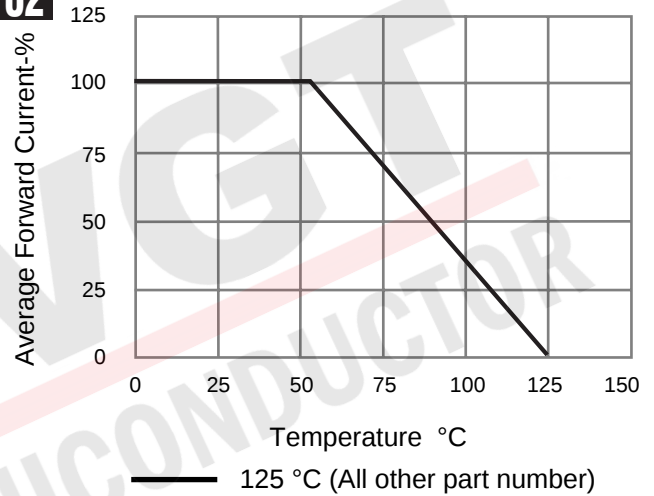


FIGURE 03 Positive Characteristic Curve

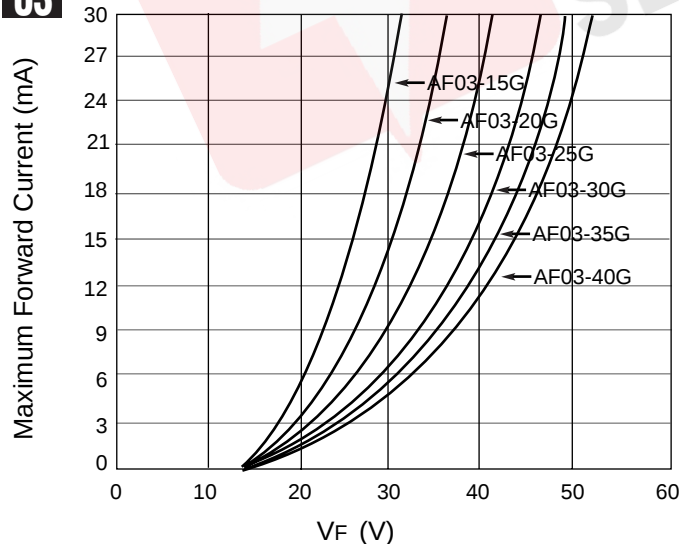


FIGURE 04 Reverse Leakage Current Curve With Voltage Variation

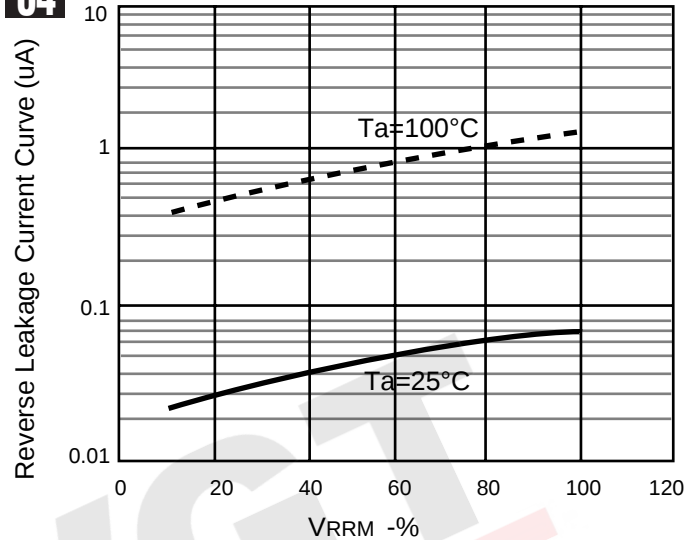
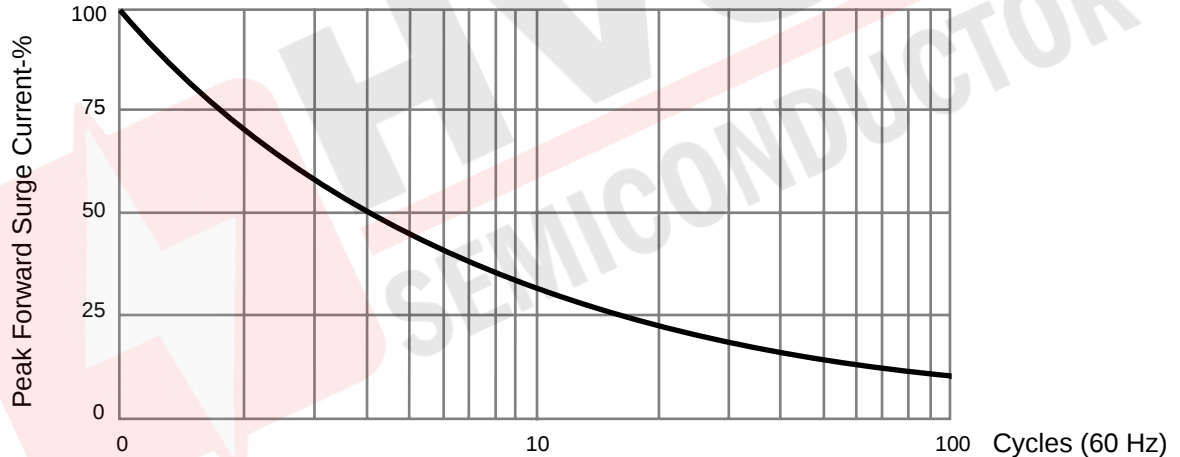


FIGURE 05 Repetitive Surge Current Derating Curve



This curve represents the percentage of published maximum surge rating as a function of surge repetition.

Note: Specifications subject to change without notice. Photo is representation only.
 Standard package quantity: 1,000PCS/in Box.